

N-Channel Enhancement Mode Field Effect Transistor

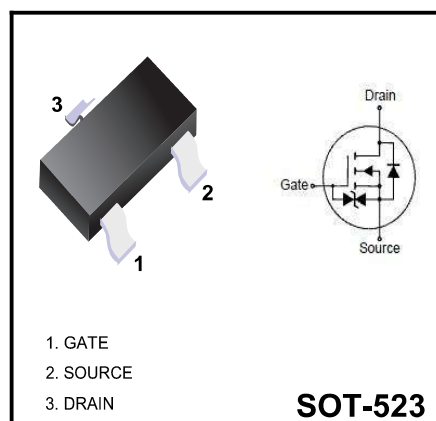
Features

- ◆ Low on resistance $R_{DS(ON)}$
- ◆ Low gate threshold voltage
- ◆ Low input capacitance
- ◆ ESD protected up to 2KV

Marking Code

2N7002KT

72K



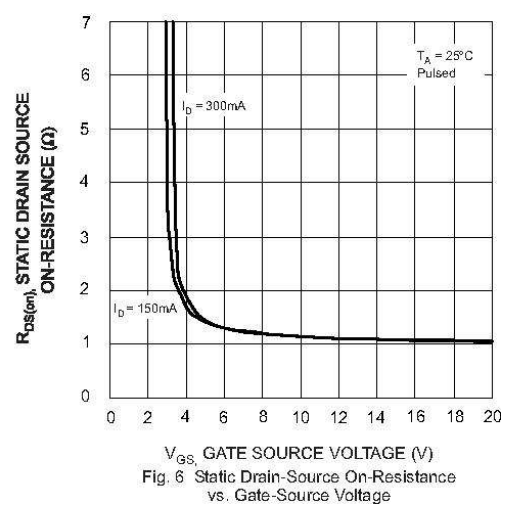
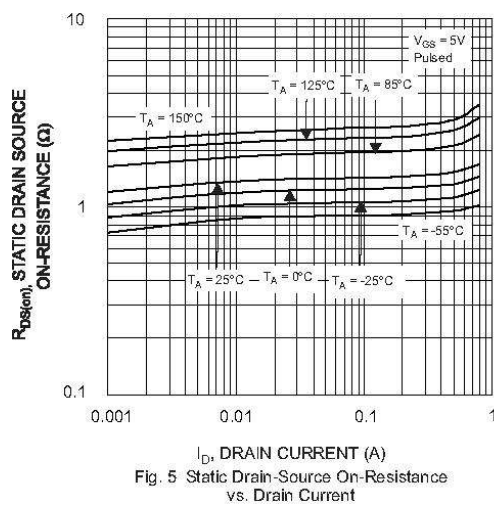
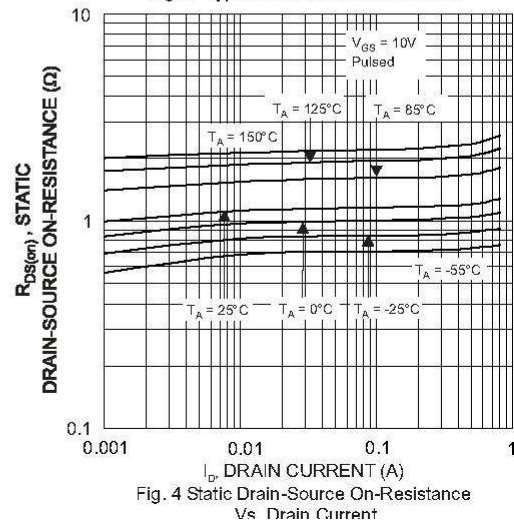
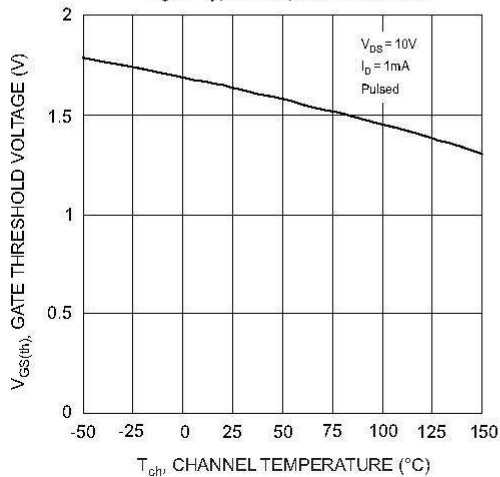
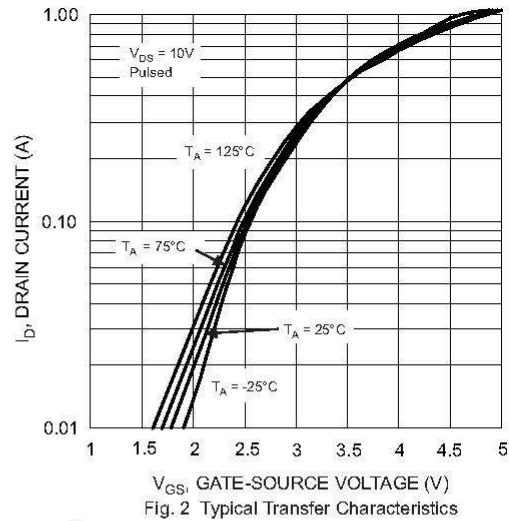
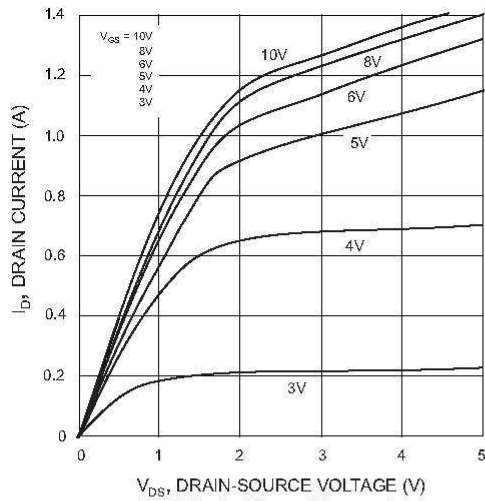
Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Continuous)	I_D	300	mA
Drain Current (Pulse Width $\leq 10 \mu\text{s}$)	I_{DM}	800	mA
Total Power Dissipation	P_{tot}	350	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Drain Source Breakdown Voltage at $I_D = 10 \mu\text{A}$	BV_{DSS}	60	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 60 \text{ V}$	I_{DSS}	-	1	μA
Gate Source Leakage Current at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	± 10	μA
Gate Threshold Voltage at $V_{DS} = 10 \text{ V}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	1	2.5	V
Static Drain Source On-Resistance at $V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$ at $V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$	$R_{DS(ON)}$	- -	3 4	Ω
Forward Transconductance at $V_{DS} = 10 \text{ V}, I_D = 200 \text{ mA}$	g_{fs}	80	-	mS
Input Capacitance at $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	50	pF
Output Capacitance at $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	25	pF
Reverse Transfer Capacitance at $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	5	pF

Typical characteristics



Ordering information

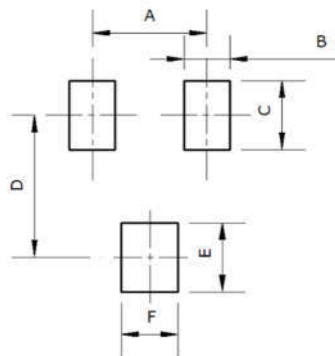
Package	Packing Description	Base Quantity	Packing Quantity
SOT-523	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-523

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	1.50	1.70	59	67
B	0.75	0.85	30	33
C	1.45	1.75	57	69
D	0.50TYP		0.020TYP	
E	0.90	1.10	35	43
G	0.00	0.10	0	4
H	0.60	0.80	24	31
J	0.10	0.20	4	8
K	0.15	0.35	6	14
L	0.26	0.46	10	18

The recommended mounting pad size



Millimeter (mm)	
Dim.	TYP
A	1.00
B	0.40
C	0.60
D	1.24
E	0.60
F	0.50

Disclaimer

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